



AO3460

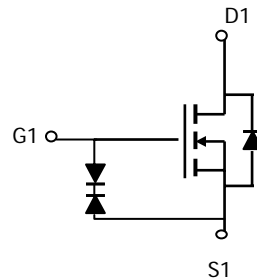
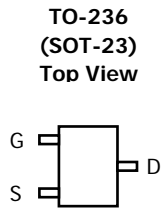
N-Channel Enhancement Mode Field Effect Transistor

General Description

The AO3460/L uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge, and operation with gate voltages as low as 4.5V, in the small SOT-23 footprint. It can be used for a wide variety of applications, including load switching, low current inverters and low current DC-DC converters. It is ESD protected. *AO3460 and AO3460L are electrically identical.*
-RoHS Compliant
-AO3460L is Halogen Free

Features

V_{DS} (V) = 60V
 I_D = 0.65A (V_{GS} = 10V)
 $R_{DS(ON)} < 1.7\Omega$ (V_{GS} = 10V)
 $R_{DS(ON)} < 2\Omega$ (V_{GS} = 4.5V)



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^{A, F}	I_D	$T_A=25^\circ\text{C}$	A
		$T_A=70^\circ\text{C}$	
Pulsed Drain Current ^B	I_{DM}	1.6	
Power Dissipation ^A	P_D	$T_A=25^\circ\text{C}$	W
		$T_A=70^\circ\text{C}$	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	70	90	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^A		Steady-State	100	125
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	63	80	$^\circ\text{C/W}$

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units	
STATIC PARAMETERS							
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	60			V	
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=60\text{V}$, $V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			1	μA	
					5		
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 20\text{V}$			± 10	μA	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	1	2.2	2.5	V	
$I_{D(ON)}$	On state drain current	$V_{GS}=10\text{V}$, $V_{DS}=5\text{V}$	1.6			A	
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}$, $I_D=0.65\text{A}$ $T_J=125^\circ\text{C}$		1.4	1.7	Ω	
			$V_{GS}=4.5\text{V}$, $I_D=0.5\text{A}$		1.6		2
g_{FS}	Forward Transconductance	$V_{DS}=5\text{V}$, $I_D=0.65\text{A}$		0.8		S	
V_{SD}	Diode Forward Voltage	$I_S=0.1\text{A}$, $V_{GS}=0\text{V}$		0.8	1	V	
I_S	Maximum Body-Diode Continuous Current				1.2	A	
DYNAMIC PARAMETERS							
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}$, $V_{DS}=30\text{V}$, $f=1\text{MHz}$		22	27	pF	
C_{oss}	Output Capacitance				6		pF
C_{rss}	Reverse Transfer Capacitance				2		pF
SWITCHING PARAMETERS							
$t_{D(on)}$	Turn-On Delay Time	$V_{GS}=10\text{V}$, $V_{DS}=30\text{V}$, $R_L=75\Omega$, $R_{GEN}=3\Omega$		5.3		ns	
t_r	Turn-On Rise Time			2.8		ns	
$t_{D(off)}$	Turn-Off Delay Time			19.7		ns	
t_f	Turn-Off Fall Time			5.5		ns	
t_{rr}	Body Diode Reverse Recovery Time	$I_F=0.65\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$, $V_{GS}=-9\text{V}$		11.3	14	ns	
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=0.65\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$, $V_{GS}=-9\text{V}$		7.5		nC	

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

C: The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using $<300\mu\text{s}$ pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The SOA curve provides a single pulse rating.

F: The current rating is based on the $t \leq 10\text{s}$ thermal resistance rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

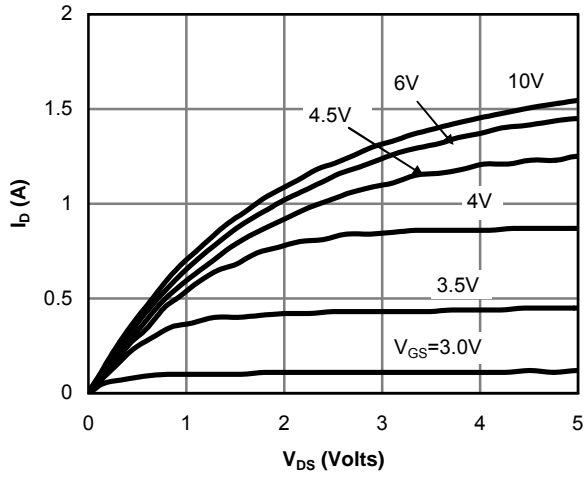


Figure 1: On-Region Characteristics

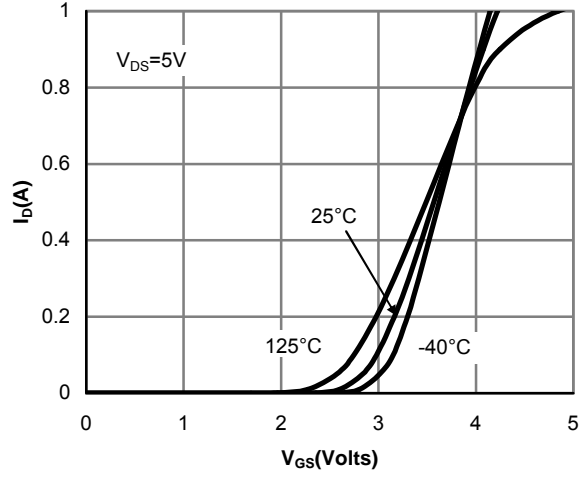


Figure 2: Transfer Characteristics

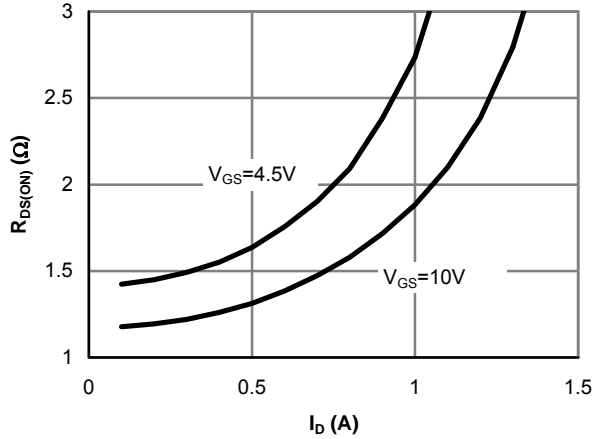


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

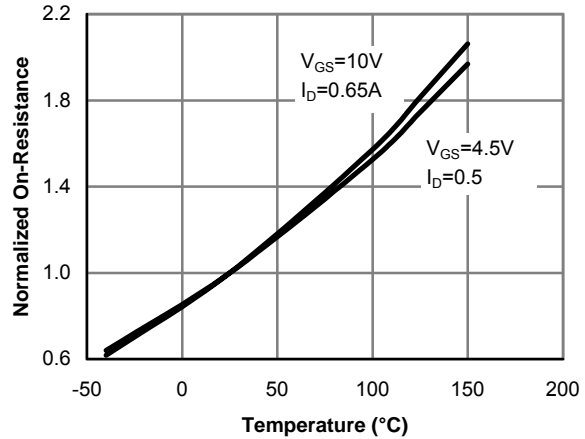


Figure 4: On-Resistance vs. Junction Temperature

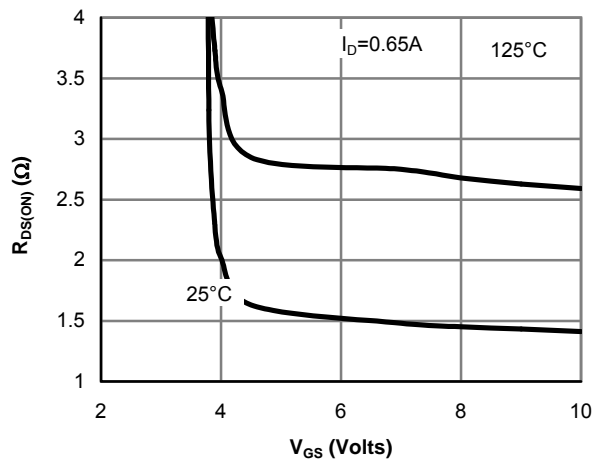


Figure 5: On-Resistance vs. Gate-Source Voltage

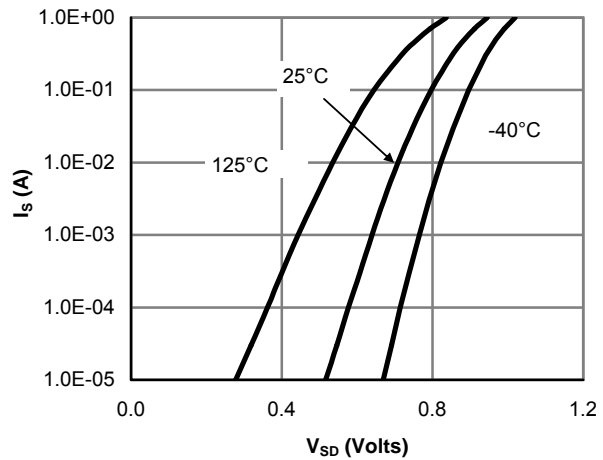


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

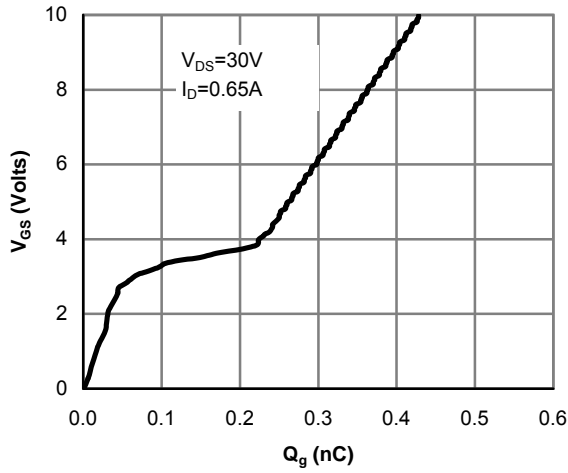


Figure 7: Gate-Charge Characteristics

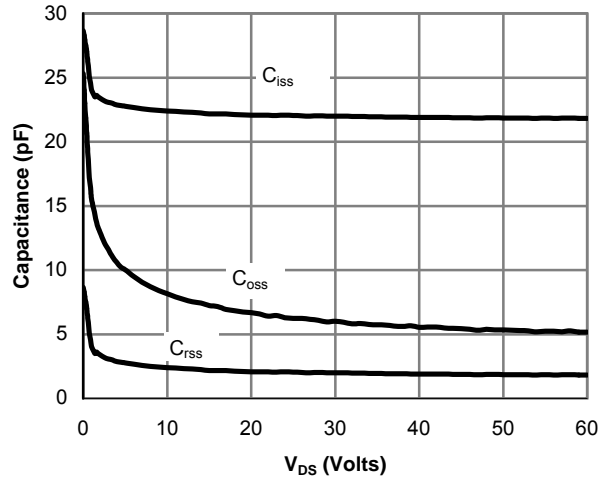


Figure 8: Capacitance Characteristics

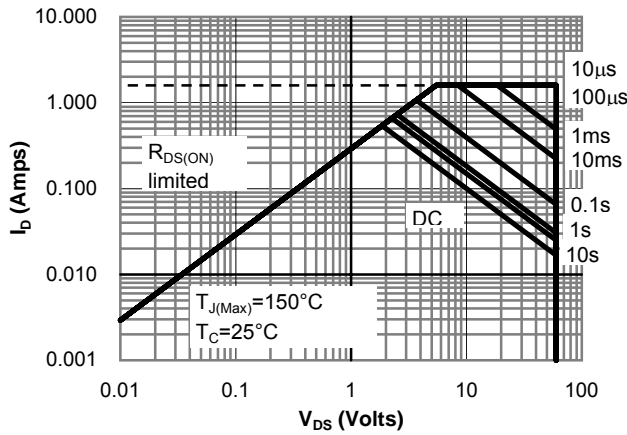


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

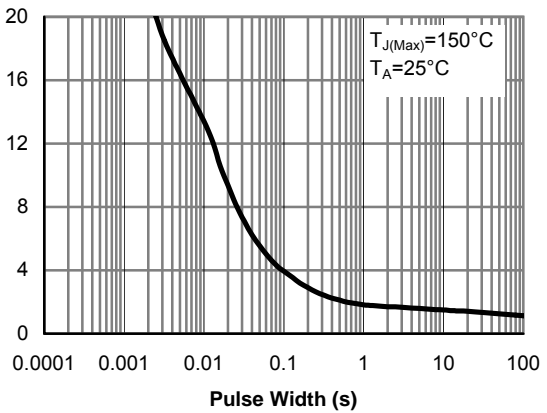


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

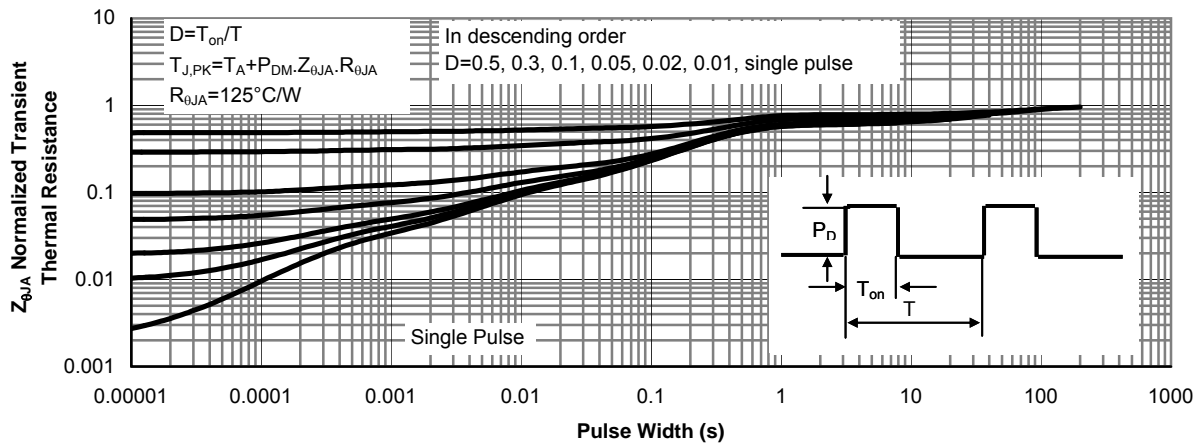


Figure 11: Normalized Maximum Transient Thermal Impedance